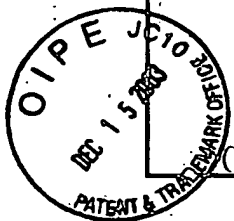


Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No. UNTYP009 Applicant: Rinerson et al. Filing Date July 1, 2003	Application No.: 10/612,191 Group 2818
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Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>Dr</i>	A	Liu, S.Q., et al., " <i>Electric-pulse-induced reversible resistance change effect in magnetoresistive films</i> ", Applied Physics Letters, Vol. 76, No. 19, 8 May 2000, 2749-2651.
<i>Dr</i>	B	Liu, S.Q., et al., " <i>A New Concept For Non-Volatile Memory: Electric-Pulse Induced Reversible Resistance Change Effect In Magnetoresistive Films</i> ", Space Vacuum Epitaxy Center, University of Huston, Huston TX, 7 Pages.
Examiner <i>Tuan T. Nguyen</i>	Date Considered <i>1/7/05</i>	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Form 1449 (Modified)	Atty Docket No. UNTP009	Application No.: 10/612,191
Information Disclosure Statement By Applicant	Applicant: Rinerson et al.	
(Use Several Sheets if Necessary)	Filing Date July 1, 2003	Group 2818

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	B	5,920,500	1999-07-06	Tehrani et al.			
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Dw	L	Beck, A. et al., "Reproducible switching effect in thin oxide films for memory applications", Applied Physics Letters, Vol. 77, No. 1, 3 July 2000, 139-141.
	M	Rossel, C. et al., "Electrical current distribution across a metal-insulator-metal structure during bistable switching", Journal of Applied Physics, Vol. 90, No. 6, 15 September 2001, 2892-2898.
Dw	N	Watanabe, Y. et al., "Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO ₃ single crystals", Applied Physics Letters, Vol. 78, No. 23, 4 June 2001, 3738-3740.
Examiner TUAN T. NGUYEN		Date Considered 11/7/05

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.